TOSHIBA {DISCRETE/OPTO}

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12526KE08H	共成市	j CD I SCF	RETE/OF	۲ОУ		99D	167		D		
Toshihu SEMIC	CON	IDUCTC	T - 39 - 13 TOSHIBA FIELD EFFECT TRANSISTOR								
/oshiha =	•••					2 S K 5					
TECH	INICA					N N CHAN $(\pi - N)$		S TYPE			
					<u>/E</u>]						
HIGH SPEED, HIGH						10	DUSTRI	AL Arr	Unit i		
SWITCHING REGULA		DC-DC CON	IVERTER AND MOTOR				<u>15.9 M</u>	AX.	<u>عە∓ەت</u>		
FEATURES:							┝┝ᡔ᠋᠇	╤┽╧╹	<u>↓</u>		
. Low Drain-Sour			•	•	-	1 .	「ᡟ₄笄	ᢞᡰ᠆		門	
				ance : Y _{fs} = 6.5S(Typ.)				`∉		4	
. Low Leakage C	100nA(Max.	00nA(Max.) @ VGS=±20V 5					08 %	UI			
IDSS=300µA(Max.) @ V _{DS} =150V						+	-14 Y	.₩	c.0		
. Enhancement-Mode : $V_{th}=1.5 \sim 3.5V \ (I_D=1mA)$						<u>20:1</u> +03	- <u>1</u>		05±		
MAXIMUM RATINGS	(Ta=2	5°C)				+03	5- -		~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~		
CHARACTE			SYMBOL	RATING	UNIT			5451	<u>+02</u>		
Drain-Source Vol	ltage	·	V _{DSX}	150	v	<u></u>		8		ł	
Gate-Source Volt			V _{GSS}	±20	v	G I.H					
Drain Current		DC	ID	15		1 -					
		Pulse	IDP	30	A		1. JATE				
Drain Power Diss	sipatio	on	· PD	100	W		2. DRAI 3. SOUR	IN (HEAT	SINKJ		
(Tc=25°C) Channel Temperat					°C	JEDEC	JEDEC -				
			T _{ch}	150 -55~150	°C °C	EIAJ					
Storage Temperature Range			Tstg	Istg -55~150 C TOSHIBA 2-16C1B Weight : 4.6g						3	
ELECTRICAL CHARA	CTERIS	STICS (Ta:	=25°C)								
CHARACTERISTIC			SYMBOL	TEST CONDITION			MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current			I _{GSS}	$V_{GS}=\pm 20V$, $V_{DS}=0$			-	-	±100	nA	
Drain Cut-off Current			IDSS	V _{DS} =150V, V	-	-	300	μA			
Drain-Source Breakdown Voltage			V(BR)DSS	ID=10mA, V(150	[-]	-	v			
Gate Threshold Voltage			Vth	V _{DS} =10V, II	1.5	-	3.5	v			
Forward Transfer Admittance			Yfs	V _{DS} =10V, I _I	3.5	6.5	-	S			
Drain-Source ON Resistance			RDS(ON)	ID=10A, VGS	-	0.12	0.18	Ω			
Drain-Source ON	Drain-Source ON Voltage			ID=15A, VGS	-	1.8	2.8	v			
Input Capacitance			Ciss	V _{DS} =10V, V _C	;s=0, f	f=1MHz	-	1100	1500	pF	
Reverse Transfer	Capac	itance	Crss	V _{DS} =10V, V _G	;s=0, f	i=1MHz	-	310	430	pF	
Output Capacitance			Coss	V _{DS} =10V, V _G	;s=0, f	=1Milz	-	630	850	pF	
L'	Ríse T	'ime	tr	10V 🗖 V	т <u>р</u> =	10A	!	110	220	ns	
4 1 -	Turn-on Time		ton		*	-	130	260	ns		
Switching Time				10 <i>µ</i> a õ≸	7 I -	1 1		100	200	ns	
Partcurug time -	Fall T	`ime	tf		V.		' i	100 1	1 200 }		
Switching lime		fime off Time		v _{IN} :t _r ,t _f <5 D.U≦1% (Cour		DD+100A	-	300	600	ns	

GT1A2

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